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¹*Graduate School of Engineering, Osaka City University, ²The SiC Division, Air Water Inc, ³Institute for Materials Research (IMR), Tohoku University, Ibaraki, ⁴Institute for Materials Research (IMR), Tohoku University, Sendai*

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¹*Advanced Technology R&D Center, Mitsubishi Electric Corporation, ²Device Technology Research Institute(AIST), ³Advanced Power Electronics Research Center (AIST), ⁴Technical Division, Kumamoto University, ⁵Faculty of Advanced Science and Technology, Kumamoto University*

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¹Frontier Research Institute for Interdisciplinary Sciences (FRIS), Tohoku University, ²Department of Electronic Engineering, Graduate school of Engineering, Tohoku University, ³Research Institute of Electrical Communication (RIEC), Tohoku University

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¹*Institute of Applied Physics, Friedrich-Schiller-University Jena*, ²*Fraunhofer Institute for Applied
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